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HMC199MS8 / 199MS8E

DUAL SPDT SWITCH DC - 2.5 GHz



Typical Applications

The HMC199MS8 / 199MS8E is ideal for:

- Cellular
- ISM Basestations
- PCS

Features

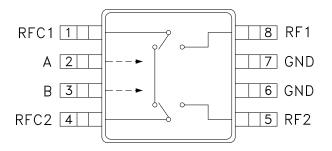
RoHS-Compliant Product Integrated Dual SPDTs

Low Insertion Loss: <0.5 dB @ 2 GHz

Positive Control: 0/+5V

Ultra Small MSOP8 Package: 14.8 mm²

Functional Diagram



General Description

The HMC199MS8 & HMC199MS8E are low-cost general purpose dual SPDT GaAs "bypass" switches in 8-lead MSOP packages covering DC to 2.5 GHz. These four-RF- port components integrate two SPDT switches and a through line onto a single IC. The designs provide low insertion loss of less than 0.5 dB while switching passive or active external circuit components in and out of the signal path. Port to port isolations are typically 25 to 30 dB. On-chip circuitry enables positive voltage control operation at very low DC currents with control inputs compatible with CMOS and most TTL logic families. Applications include LNA or filter bypass switching and single bit attenuator switching. The HMC199MS8E is a RoHS-compliant product.

Electrical Specifications, $T_{\Delta} = +25^{\circ}$ C, VctI = 0/+5 Vdc, 50 Ohm System

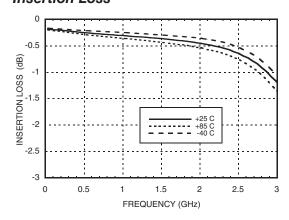
Parameter	Frequency	Min.	Тур.	Max.	Units
Insertion Loss	DC - 1.0 GHz DC - 2.0 GHz DC - 2.5 GHz		0.3 0.5 0.7	0.6 0.8 1.0	dB dB dB
Isolation	DC - 2.0 GHz DC - 2.5 GHz	22 17	25 21		dB dB
Return Loss (On State, Any Port)	DC - 2.0 GHz DC - 2.5 GHz	17 12	20 15		dB dB
Input Power for 1 dB Compression	0.5 - 2.0 GHz	19	23		dBm
Input Third Order Intercept (Two-tone Input Power = 0 dBm Each Tone)	0.5 - 2.0 GHz	32	36		dBm
Switching Characteristics	DC - 2.5 GHz				
tRISE, tFALL (10/90% RF) tON, tOFF (50% CTL to 10/90% RF)			20 40		ns ns



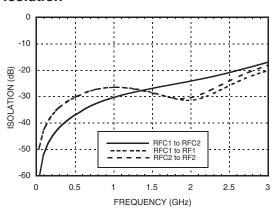


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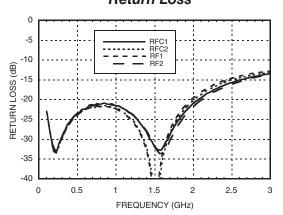
Insertion Loss



Isolation



Return Loss



Note:

Isolation between RF1 - RF2 (when RFC1 - RFC2 is in insertion loss state) is 25 dB @ 1 GHz and 17 dB @ 2 GHz.



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Compression vs. Frequency

	Carrier at 900MHz		Carrier at 1900MHz		
CTL Input	Input Power for 0.1 dB Compres- sion	Input Power for 1.0 dB Compres- sion	Input Power for 0.1 dB Compression	Input Power for 1.0 dB Compression	
(Vdc)	(dBm)	(dBm)	(dBm)	(dBm)	
+5	20 23.5		19	22	

Caution: Do not operate continuously at RF power input greater than 1 dB compression and do not "hot switch" power levels greater than +13 dBm (Control = 0/+5Vdc).

Distortion vs. Frequency

Control Input	Input Third Order Intercept (dBm) 0 dBm Each Tone	
(Vdc)	(Vdc) 900 MHz	
+5	34.5	37.5

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Truth Table

*Control Input Tolerances are +/- 0.5 Vdc

Control Input*		Control Current (Typical)		Signal Path		
A (Vdc)	B (Vdc)	la (uA)	lb (uA)	RFC1 to RFC2	RFC1 to RF1	RFC2 to RF2
0	+5	-65	65	ON	OFF	OFF
+5	0	65	-65	OFF	ON	ON

DC blocking capacitors are required at ports RFC1, RFC2, RF1, RF2. Choose value for lowest frequency of operation.





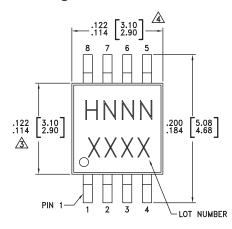
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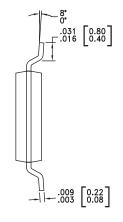
Absolute Maximum Ratings

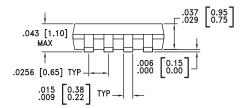
RF Input Power V _{CTL} = 0/+5V	+24 dBm	
Control Voltage Range (A & B)	-0.5 to +7.5 Vdc	
Channel Temperature	150 °C	
Thermal Resistance	172 °C/W	
Storage Temperature	-65 to +150 °C	
Operating Temperature	-40 to +85 °C	
ESD Sensitivity (HBM)	Class 1A	



Outline Drawing







NOTES:

- 1. LEADFRAME MATERIAL: COPPER ALLOY
- 2. DIMENSIONS ARE IN INCHES [MILLIMETERS].
- A DIMENSION DOES NOT INCLUDE MOLDFLASH OF 0.15mm PER SIDE.
 DIMENSION DOES NOT INCLUDE MOLDFLASH OF 0.25mm PER SIDE.
- 5. ALL GROUND LEADS MUST BE SOLDERED TO PCB RF GROUND.

Package Information

Part Number	Package Body Material	Lead Finish	MSL Rating	Package Marking [3]
HMC199MS8	Low Stress Injection Molded Plastic	Sn/Pb Solder	MSL1 [1]	H199 XXXX
HMC199MS8E	RoHS-compliant Low Stress Injection Molded Plastic	100% matte Sn	MSL1 [2]	H199 XXXX

- [1] Max peak reflow temperature of 235 $^{\circ}\text{C}$
- [2] Max peak reflow temperature of 260 °C
- [3] 4-Digit lot number XXXX

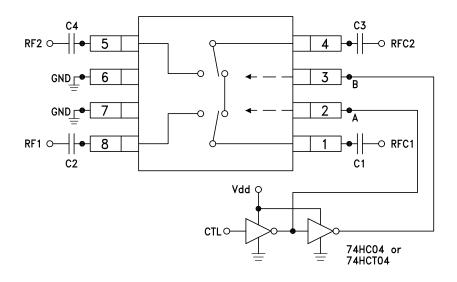


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Typical Application Circuit



Notes

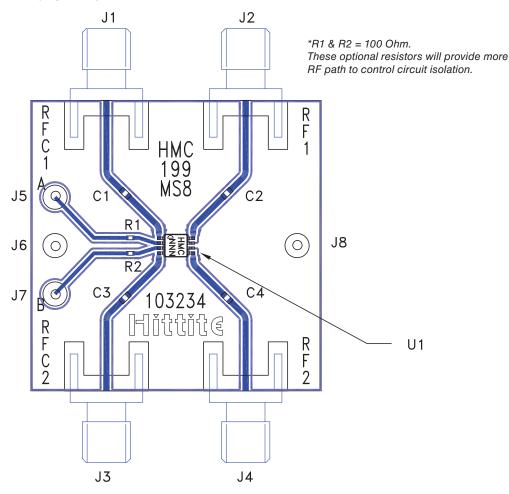
- 1. Set A/B control to 0/+5V, Vdd = +5V and use HCT series logic to provide a TTL driver interface.
- 2. Control inputs A/B can be driven directly with CMOS logic (HC) with Vdd = 5 to 7 Volts applied to the CMOS logic gates.
- 3. DC Blocking capacitors are required for each RF port as shown. Capacitor value determines lowest frequency of operation.
- 4. Highest RF signal power capability is achieved with Vdd = +7V and A/B set to 0/+7V.
- 5. For further information refer to "Using the HMC199MS8 as a Low-Cost 1-Bit Attenuator" product note.





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Eval Board Layout (Top View)



List of Materials for Evaluation PCB 103236 [1]

Item	Description
J1 - J4	PCB Mount SMA RF Connector
J5 - J8	DC Pin
C1 - C4	Chip Capacitor, 0402 Pkg. Choose value for lowest frequency of operation. 330 pF is provided on PCB.
R1 - R2	100 Ohm Resistor, 0402 Pkg.
U1	HMC199MS8 / HMC199MS8E Bypass Switch
PCB [2]	103234 Evaluation PCB 1.5" x 1.5"

^[1] Reference this number when ordering complete evaluation PCB

The circuit board used in the final application should be generated with proper RF circuit design techniques. Signal lines at the RF ports should have 50 ohm impedance. The evaluation circuit board shown above is available from Hittite Microwave Corporation upon request.

^[2] Circuit Board Material: Rogers 4350